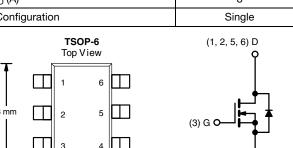


www.vishay.com

Vishay Siliconix

# Automotive N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.030				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 2.5 \text{ V}$	0.034				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 1.8 \text{ V}$	0.038				
I <sub>D</sub> (A)	8				
Configuration	Single				



Marking Code: 8Jxxx

- 2.85 mm

N-Channel MOSFET

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % Rq and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and Halogen-free	SQ3460EV-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	$V_{DS}$	20	· ·		
Gate-Source Voltage	$V_{GS}$	± 8	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	8		
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	4.8		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	4.6	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	32			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	10		
Single Pulse Avalanche Energy	L = 0.11IIII	E <sub>AS</sub>	5	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	3.6	W	
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1.2	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient P	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	110	°C/W		
Junction-to-Foot (Drain)		R <sub>thJF</sub>	41	C/VV		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Vishay Siliconix

PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static				l		l .	L
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		20		-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.4	0.6	1.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	= 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 4.5 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 5.1 A	-	0.025	0.030	
		$V_{GS} = 4.5 \text{ V}$	I <sub>D</sub> = 5.1 A, T <sub>J</sub> = 125 °C	-	-	0.045	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 5.1 A, T <sub>J</sub> = 175 °C	=.	-	0.053	Ω
		V <sub>GS</sub> = 2.5 V	I <sub>D</sub> = 4.7 A	-	0.027	0.034	
		V <sub>GS</sub> = 1.8 V	I <sub>D</sub> = 2.5 A	-	0.031	0.038	
Forward Transconductanceb	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.1 A		-	28	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	848	1060	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	-	117	146	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	68	85	
Total Gate Charge <sup>c</sup>	Qg			=.	9.3	14	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 4.5 V	$V_{DS} = 10 \text{ V}, I_{D} = 5.1 \text{ A}$	=.	1.1	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		-	1.4	-	]
Gate Resistance	R <sub>g</sub>	f = 1 MHz		6.2	12.4	18.6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			=.	8	12	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$ $I_D \cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_g$ = 1 $\Omega$		-	8	12	- ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	21	32	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	32	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 5 A, V <sub>GS</sub> = 0		-	0.77	1.2	V

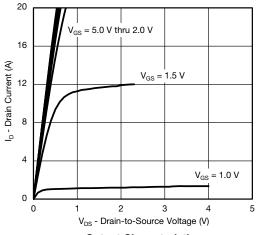
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

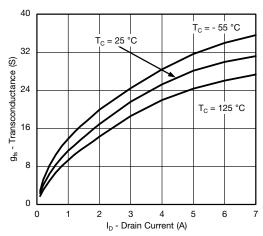
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



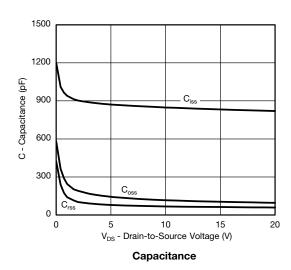
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

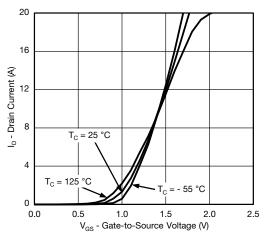


#### **Output Characteristics**

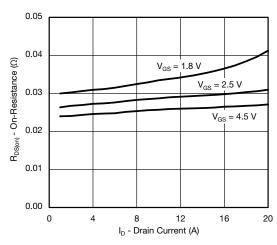


#### Transconductance

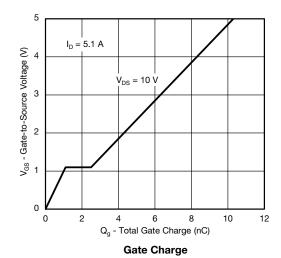




**Transfer Characteristics** 

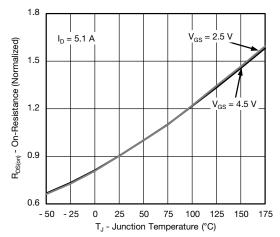


On-Resistance vs. Drain Current

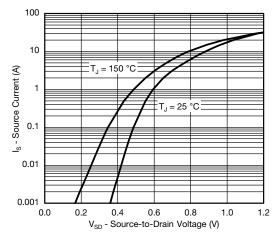




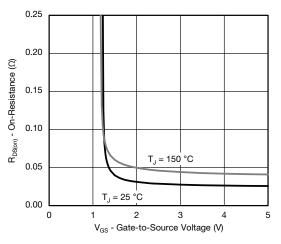
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



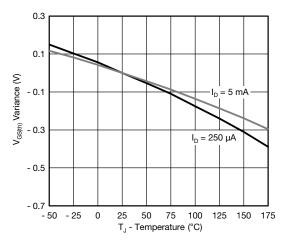
On-Resistance vs. Junction Temperature



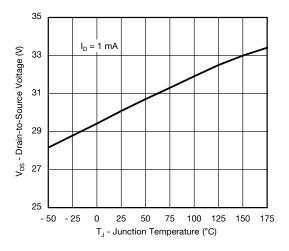
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



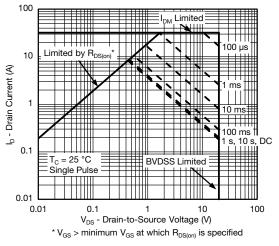
**Threshold Voltage** 



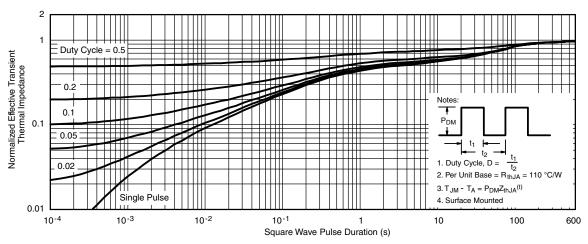
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



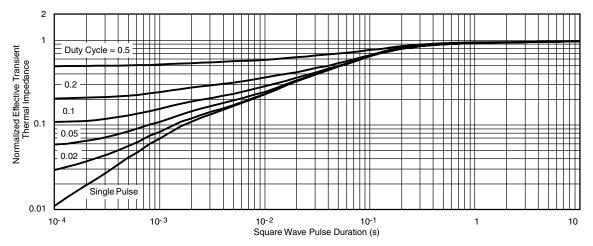
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

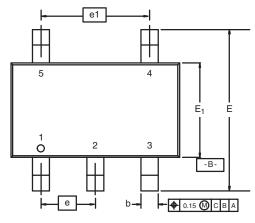
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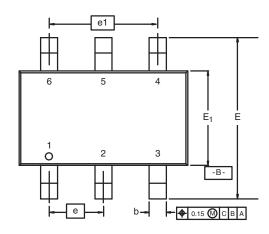




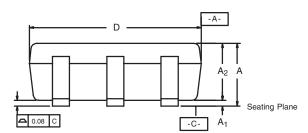
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 

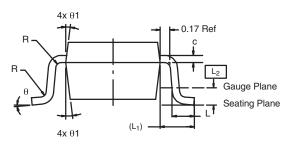




**5-LEAD TSOP** 





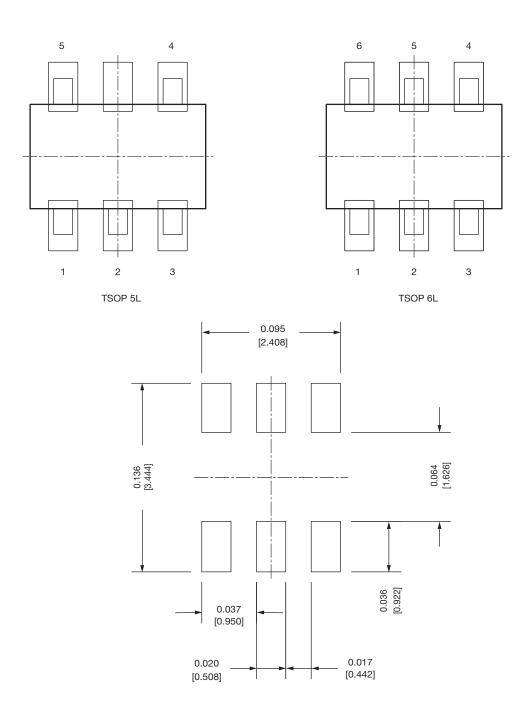


	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref			0.024 Ref			
L <sub>2</sub>		0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom				7° Nom		
ECN: C		ev. I, 18-Dec	c-06				

Document Number: 71200 18-Dec-06



## Recommended Land Pattern For TSOP-5L / TSOP-6L



#### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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